

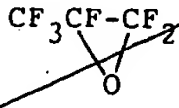
ATTACHMENT A

New Claims

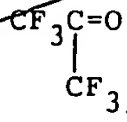
Following herewith is a clean copy of each new claim.

11. A chamber cleaning gas comprising at least one gas selected from the

group consisting of



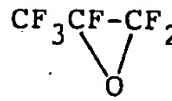
and



5,928,963
+
2002 gas

12. A chamber cleaning gas according to claim 11 comprising

hexafluoropropylene oxide represented by the formula



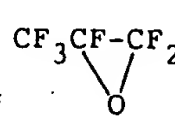
removing residue
col 1 20 es.
disclosed in
4,581,101
col 4 line 60

13. A chamber cleaning gas according to claim 11 comprising CF_3COCF_3 .

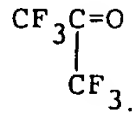
14. A chamber cleaning gas according to claim 11 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar, H_2 , N_2 and O_2 .

15. A chamber cleaning method comprising the step of treating a plasma CVD chamber of a semiconductor integrated circuit production device with at least one

chamber cleaning gas selected from the group consisting of

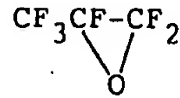


and



16. A chamber cleaning method according to claim 15 wherein the chamber

cleaning gas is hexafluoropropylene oxide represented by the formula



17. A chamber cleaning method according to claim 15 wherein the chamber cleaning gas is CF_3COCF_3 .

M

18. A chamber cleaning method according to claim 15 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar, H_2 , N_2 and O_2 .